

REMARKS

Claims 22-23, 25-27, and 30 have been amended. Claims 24 and 29 have been canceled. Claims 22-23, 25-28, 30, 33, 70-71, 74-81, 84-86, and 92-100 are now pending. Applicants reserve the right to pursue the original claims and other claims in this and other applications. Applicants respectfully request reconsideration of the above-referenced application in light of the amendments and following remarks.

At the outset, Applicants acknowledge with appreciation that claims 70, 71, 74-81, 84-86, and 92-100 are in condition for allowance. Applicants acknowledge with appreciation that claims 24 and 26-30 would be allowable if rewritten in independent form including all of the limitations of their base claim and any intervening claims. Accordingly, independent claim 22 has been amended to incorporate the allowable subject matter of dependent claim 24. Specifically, claim 22 now recites, *inter alia*, "at least one insulating spacer [is] provided over [a] polysilicon layer." Consequently, all of the pending claims, *i.e.*, claims 22-23, 25-28, 30, 33, 70-71, 74-81, 84-86, and 92-100, now contain allowable subject matter and should be in immediate condition for allowance.

Claims 22-23 and 25 stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. patent no. 5,686,331 ("Song"). The rejection is respectfully traversed.

As indicated above, the allowable subject matter of dependent claim 24 has been incorporated into independent claim 22. As such, Son does not disclose a transistor structure comprising, *inter alia*, "a semiconductor substrate; a gate stack . . . comprising: a gate oxide layer . . . a polysilicon layer . . . at least one insulating spacer provided over the polysilicon layer . . . at least one channel implant region formed underneath said gate stack, wherein said at least one insulating spacer defines at least

in part the at least one channel implant region,” as recited in amended claim 22. Claims 23 and 25 depend from claim 22 and should be similarly allowable along with claim 22 for at least the reasons provided above, and on their own merits.

Claim 33 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Son in view of U.S. patent no. 6,693,333 (“Yu”). The rejection is respectfully traversed.

Claim 33 depends from claim 22 and should be similarly allowable along with claim 22 for at least the reasons provided above, and on its own merits. In particular, Son does not disclose or suggest a transistor structure comprising, *inter alia*, “a semiconductor substrate; a gate stack . . . comprising: a gate oxide layer . . . a polysilicon layer . . . at least one insulating spacer provided over the polysilicon layer . . . at least one channel implant region formed underneath said gate stack, wherein said at least one insulating spacer defines at least in part the at least one channel implant region,” as recited in claim 22. Yu is relied upon for disclosing a silicide layer and adds nothing to rectify the deficiencies associated with Son. Namely, Son does not teach or suggest at least one insulating spacer provided over a polysilicon layer.

In view of the above, each of the presently pending claims in this application is believed to contain allowable subject matter and should be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to review and pass this application to issue.

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Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorney for Applicants